Small Signal Low Noise Transistors (PNP)

TO-92

Description

- The 2N4126 is PNP silicon epitaxial planar transistors designed for general purpose switching and amplifier applications.

Features

- Complementary to 2N4124
- High power PT:625mW at 25°C
- High DC current Gain hFE:120~360 at Ic=2mA

Maximum Ratings *($T_{Ambient}$=25ºC unless noted otherwise)*

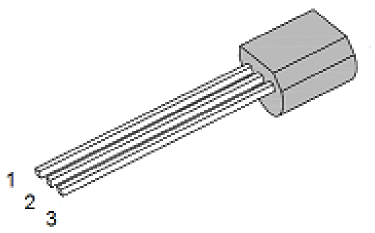
Symbol	Description	2N4126	Unit
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{CBO}	Collector-Base Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-4.0	V
I_C	Collector Current Continuous	-200	mA
P_D	Power Dissipation at T_A=25°C	625	mW
T_J	Junction Temperature	+150	° C
T_{STG}	Storage Temperature Range	-55 to +150	° C

Electrical Characteristics *($T_{Ambient}$=25ºC unless noted otherwise)*

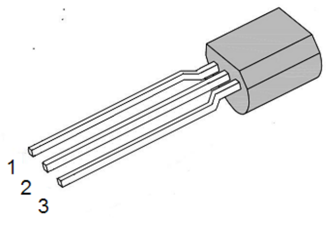
Symbol	Description	2N4126			Unit	Conditions
		Min.	Typ.	Max.		
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	-25	-	-	V	I_C=-10μA, I_E=0
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	-25	-	-	V	I_C=-1mA, I_B=0
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	-4.0	-	-	V	I_E=-10μA, I_C=0
I_{CBO}	Collector Cutt-off Current	-	-	-50	nA	V_{CB}=-20V, I_E=0
I_{EBO}	Emitter Cutt-off Current	-	-	-50	nA	V_{BE}=-3V, I_C=0
$V_{CE(sat)}$*	Collector Emitter Saturation Voltage	-	-	-400	V	I_C=-50mA, I_B=-5mA
$V_{BE(sat)}$*	Base Emitter Saturation Voltage	-	-	-950	V	I_C=-50mA, I_B=-5mA
h_{FE}*	D.C. Current Gain	120	-	360		V_{CE}=-1V, I_C=-2mA
		60	-	-		V_{CE}=-1V, I_C=-50mA
f_T	Current Gain-Bandwidth Product	250	-	-	MHz	V_{CE}=-20V, I_C=-10mA, f=100MHz
NF	Noise Figure	-	-	4.0	dB	V_{CE}=-5V I_C=-100uA, R_S=1.0KΩ,f=10Hz to15.7KHz
C_{ob}	Output Capacitance	-	-	4.5	pF	V_{CB}=-5V, I_E=0 f=1MHz

*Pulse Test: Pulse Width≤380μs, Duty Cycle≤2%

Pin Configuration

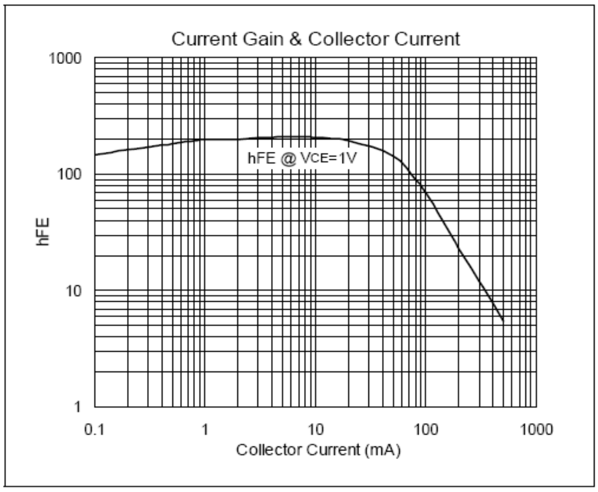


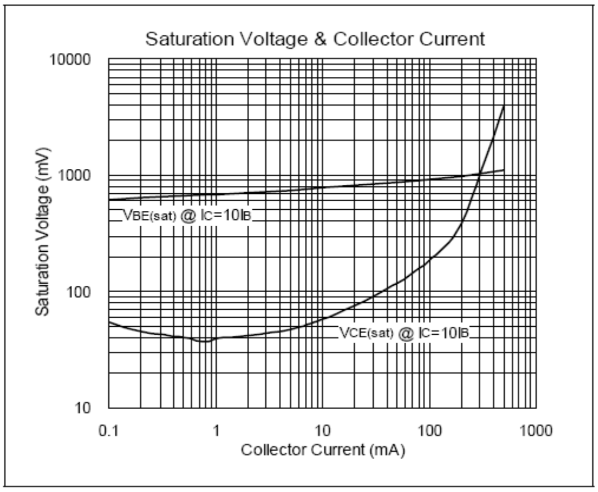
1: Emitter 2: Base 3: Collector

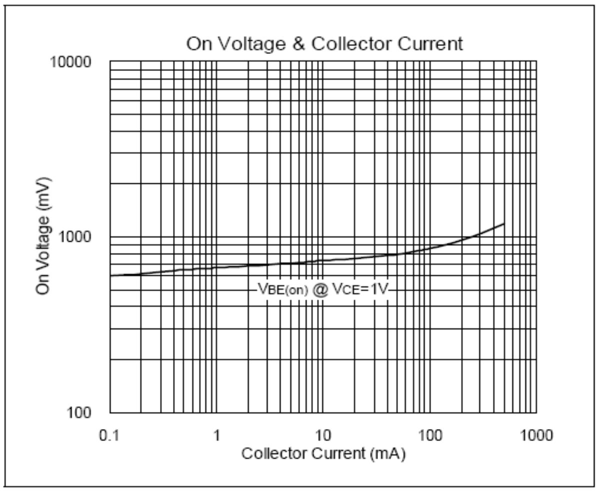


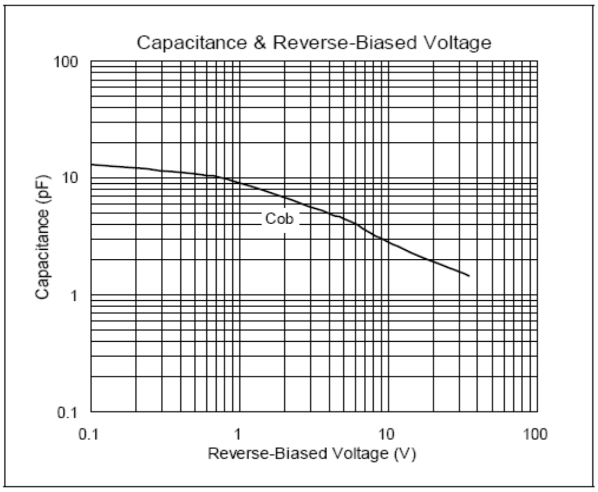
1: Emitter 2: Base 3: Collector

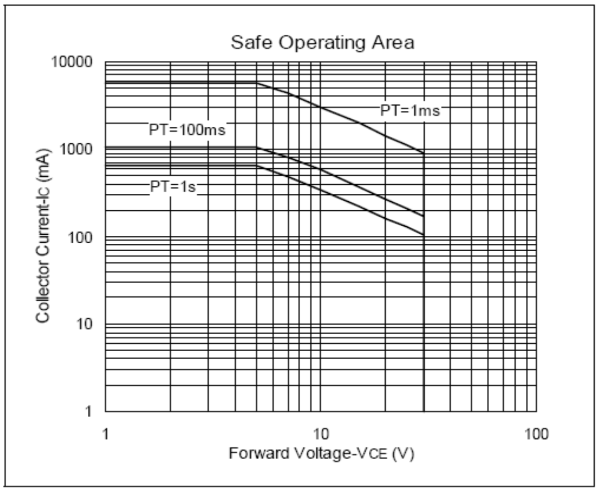
Characteristics Curves

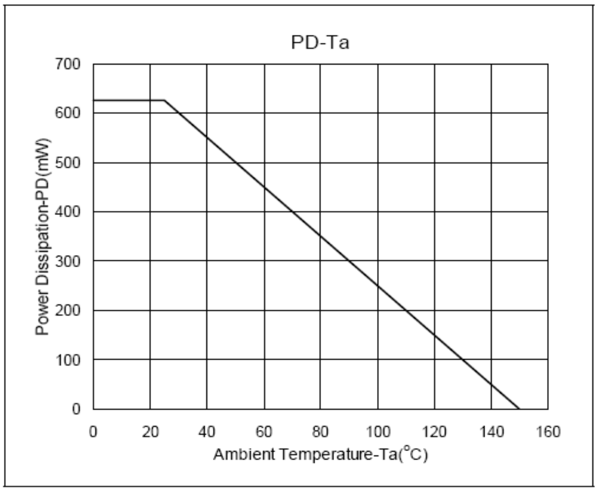




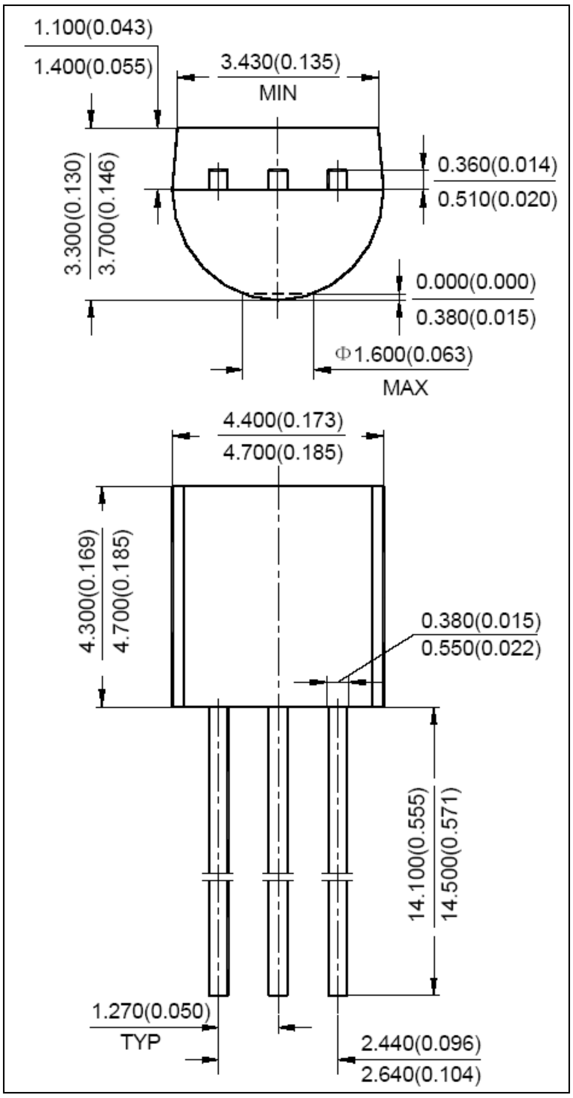




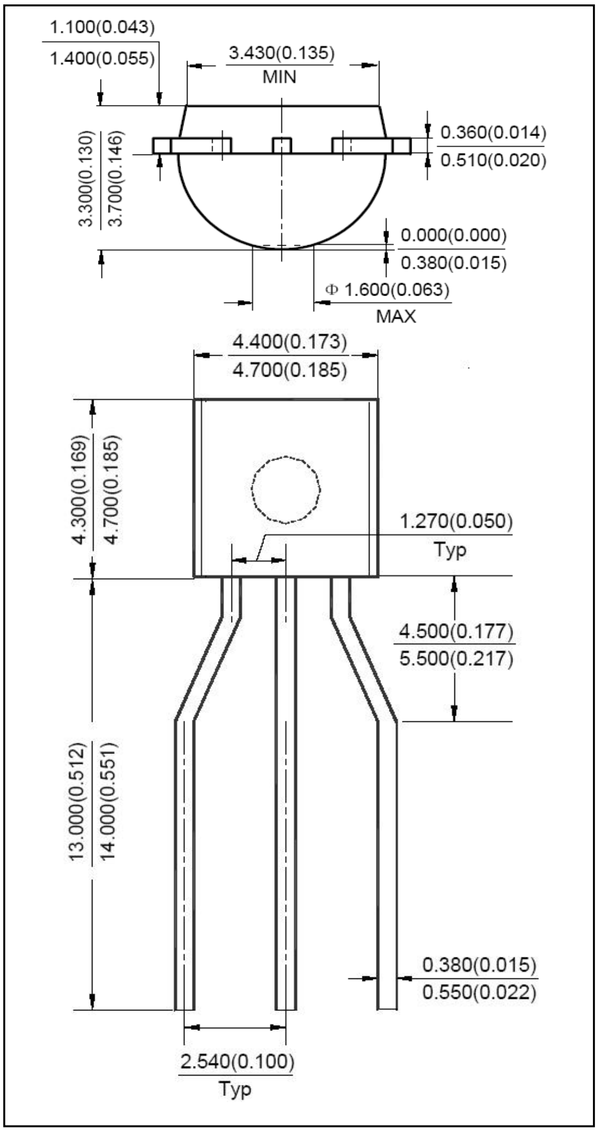




Dimensions in mm (Inch)



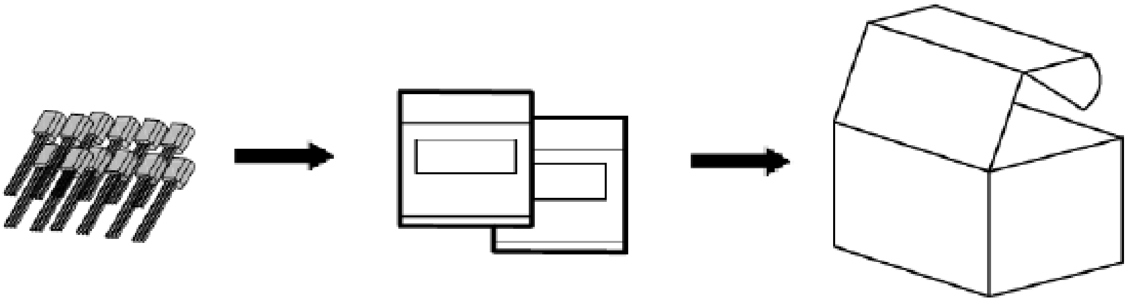
TO-92 Buck



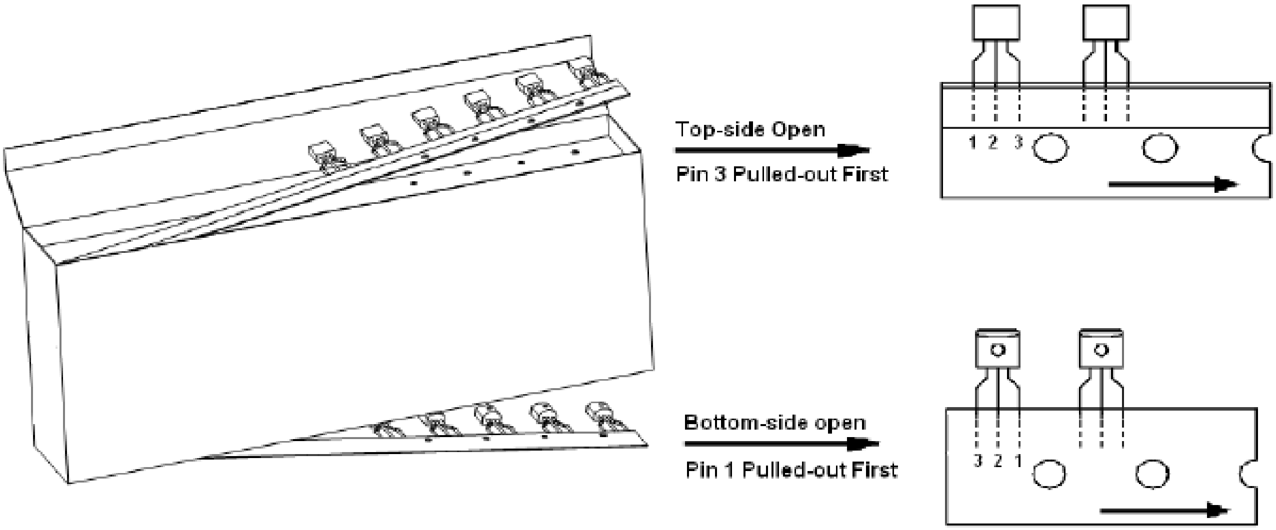
TO-92 Ammo

Packing information

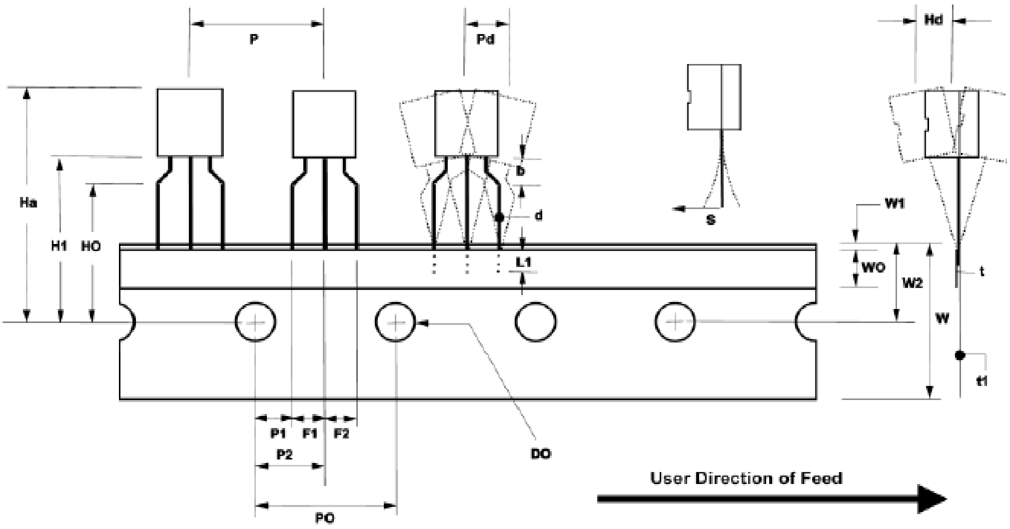
Bulk Packing: 1K/Polybag and 2K/Inner Box



Tape and Ammo Packing:2K/Ammo Box



Tape and Ammo Dimensions



Item Description	Symbol	Dimensions	
		inch	mm
Base of Package to Lead Bend	b	0.118+/-0.015	3.00+/-0.40
Component Height	Ha	0.945+/-0.02	24.00+/-0.50
Lead Clinch Height	H0	0.63+/-0.016	16.00+/-0.40
Component Base Height	H1	0.748+/-0.015	19.00+/-0.40
Component Alignment (side/side)	Pd	0.314 max.	0.80 max.
Component Alignment (front/back)	Hd	0.039 max.	1.00 max.
Component Pitch	P	0.5+/-0.024	12.70+/-0.60
Feed Hole Pitch	P0	0.5+/-0.008	12.70+/-0.20
Hole Center to First Lead	P1	0.147+/-0.012	3.75+/-0.30
Hole Center to Component Center	P2	0.25+/-0.012	6.35+/-0.30
Lead Spread	F1/F2	0.104+0.01/-0.009	2.60+0.30/-0.20
Lead Thickness	d	0.017+0.04/-0.001	0.45+1.00/-0.05
Taped Lead Length	L1	0.098 max.	2.50 max.
Taped Lead Thickness	t	0.027+/-0.008	0.70+/-0.20
Carrier Tape Thickness	t1	0.015+/-0.002	0.40+/-0.05
Carrier tape Width	W	0.728+/-0.008	18.50+/-0.20
Hold-down Tape Width	W0	0.236+/-0.015	6.00+/-0.40
Hold-down Tape Position	W1	0.011+0.008/-0.11	0.30+0.20/-0.30
Feed Hole Position	W2	0.354+/-0.016	9.00+/-0.40
Sprocket Hole Diameter	D0	0.157+/-0.008	4.00+/-0.20
Lead Spring Out	S	0.016 max.	0.40 max.

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